

SEMICONDUCTOR NONVOLATILE MEMORY AND FABRICATION THEREOF

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Abstract of JP7106446

PURPOSE: To provide a semiconductor nonvolatile memory, and fabrication method thereof, suitable for high integration in which the gate length can be shortened.

CONSTITUTION: In the semiconductor nonvolatile memory having a laminate structure of floating gate and control gate with a select gate being located contiguously thereto, the select gate 23 is formed on a semiconductor substrate 21 through a gate oxide 22. A tunnel oxide 24 thinner than the gate oxide 22, an L-shaped floating gate 25a contiguous to the tunnel oxide 24, and an L-shaped insulation film 26a contiguous to the floating gate 25a are also deposited at least on one side of the select gate 23. A side wall type laminate comprising a substantially square control gate 25a is also provided contiguously to the insulation film 26a thus shortening the first gate length L11 being defined by the floating gate 25a and the control gate 27.

